

N-channel 25 V 4.5 mΩ logic level MOSFET in LFPAK Rev. 01 — 2 December 2010 Product

Product data sheet

#### 1. **Product profile**

#### **1.1 General description**

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising Superjunction technology
- Ultra low QG, QGD & QOSS for high system efficiencies at low and high loads

Server power supplies

Sync rectifier

### 1.3 Applications

- DC-to-DC converters
- Load switching
- Power OR-ing

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	25	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	-	-	84	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	61	W
Tj	junction temperature		-55	-	175	°C
Static cha	racteristics					
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	4.5	5.8	mΩ
	resistance	$V_{GS}$ = 10 V; $I_D$ = 20 A; $T_j$ = 25 °C; see <u>Figure 12</u>	-	3.5	4.5	mΩ



### N-channel 25 V 4.5 mΩ logic level MOSFET in LFPAK

Table 1.	e 1. Quick reference data continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 20 \text{ A}; \\ V_{DS}  12 \text{ V}; \text{ see } \underline{\text{Figure } 14}; \\ \text{see } \underline{\text{Figure } 15} \end{array}$	-	3.5	-	nC
Q <sub>G(tot)</sub>	total gate charge	$\label{eq:V_GS} \begin{array}{l} V_{GS} = 4.5 \; V; \; I_{D} = 20 \; A; \\ V_{DS} = 12 \; V; \; see \; \underline{Figure \; 14}; \\ see \; \underline{Figure \; 15} \end{array}$	-	10.9	-	nC

### 2. Pinning information

Table 2.	Pinning	j information				
Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	S	source		_		
2	S	source	mb ()	D D		
3	S	source				
4	G	gate				
mb	D	mounting base; connected to drain		mbb076 S		
SOT669 (LFPAK)						

### 3. Ordering information

Type number	Package			
	Name	Description	Version	
PSMN4R0-25YLC	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669	

N-channel 25 V 4.5 mΩ logic level MOSFET in LFPAK

#### **Limiting values** 4.

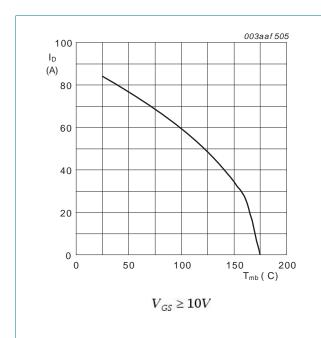
#### **Limiting values** Table 4.

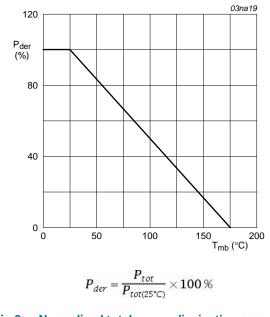
In accordance with the Absolute Maximum Rating System (IEC 60134).

$\begin{array}{c c c c c c c c c c c c c c c c c c c $			<b>391</b>			
$ \begin{array}{cccc} V_{DGR} & drain-gate voltage & 25\ ^{\circ}C \leq T_{j} \leq 175\ ^{\circ}C;\ R_{GS} = 20\ k\Omega & - & 25 \\ V_{GS} & gate-source voltage & -20 & 20 \\ I_{D} & drain current & V_{GS} = 10\ V;\ T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 1 & - & 84 \\ V_{GS} = 10\ V;\ T_{mb} = 100\ ^{\circ}C;\ see\ Figure\ 1 & - & 60 \\ I_{DM} & peak\ drain\ current & pulsed;\ t_{p} \leq 10\ \mu s;\ T_{mb} = 25\ ^{\circ}C; \\ see\ Figure\ 4 & voltage\ 10\ \mu s;\ T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 1 & - & 61 \\ T_{stg} & storage\ temperature & -55 & 175 \\ T_{j} & junction\ temperature & -55 & 175 \\ T_{std(M)} & peak\ soldering\ temperature & -55 & 175 \\ T_{std(M)} & peak\ soldering\ temperature & - & 260 \\ V_{ESD} & electrostatic\ discharge\ voltage & MM\ (JEDEC\ JESD22-A115) & 200 & - \\ \hline \hline Source-drain\ tiode & \\ I_{SM} & peak\ source\ current & T_{mb}\ 25\ ^{\circ}C & - & 336 \\ I_{SM} & peak\ source\ current & pulsed;\ t_{p}\ \leq 10\ \mu s;\ T_{mb}\ = 25\ ^{\circ}C & - & 336 \\ \hline \ Avalanche\ rugedness & \\ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	Symbol	Parameter	Conditions	Min	Max	Unit
$\begin{array}{cccc} V_{GS} & \mbox{gate-source voltage} & -20 & 20 \\ I_D & \mbox{drain current} & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^{\circ}C; \ see \ Figure 1 & -84 \\ V_{GS} = 10 \ V; \ T_{mb} = 100 \ ^{\circ}C; \ see \ Figure 1 & -60 \\ I_{DM} & \mbox{peak drain current} & \mbox{pulsed; } t_p \le 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}C; \ see \ Figure 2 & -86 \\ P_{tot} & \ total \ power \ dissipation & T_{mb} = 25 \ ^{\circ}C; \ see \ Figure 2 & -86 \\ P_{tot} & \ total \ power \ dissipation & T_{mb} = 25 \ ^{\circ}C; \ see \ Figure 2 & -86 \\ P_{tot} & \ total \ power \ dissipation & T_{mb} = 25 \ ^{\circ}C; \ see \ Figure 2 & -86 \\ T_{stg} & \ storage \ temperature & -55 & 175 \\ T_{j} & \ junction \ temperature & -55 & 175 \\ T_{sld(M)} & \ peak \ soldering \ temperature & -55 & 175 \\ P_{cSD} & \ electrostatic \ discharge \ voltage & \ MM \ (JEDEC \ JESD22 \ A115) & 200 & - \\ \hline Source-drain \ diode & & \\ I_S & \ source \ current & \ T_{mb} = 25 \ ^{\circ}C & -86 \\ I_{SM} & \ peak \ source \ current & \ pulsed; \ t_p \le 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}C & -86 \\ \hline Avalanche \ ruge \ discharge \ $	V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	25	V
$\begin{split} & \text{I}_{D} & \text{drain current} & \begin{array}{c} V_{\text{GS}} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 1} & - & 84 \\ \hline V_{\text{GS}} = 10 \ \text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C}; \ \text{see Figure 1} & - & 60 \\ \hline I_{DM} & \text{peak drain current} & \begin{array}{c} \text{pulsed}; \ t_p \leq 10 \ \mu\text{s}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \\ \text{see Figure 4} & \end{array} & - & \begin{array}{c} 336 \\ 10 \ \text{mm} & 100 \ ^{\circ}\text{C}; \ \text{see Figure 1} & - & 61 \\ \hline T_{stg} & \text{storage temperature} & - & 61 \\ \hline T_{stg} & \text{storage temperature} & -55 & 175 \\ \hline T_{j} & \text{junction temperature} & -55 & 175 \\ \hline T_{sld(M)} & \text{peak soldering temperature} & - & 260 \\ \hline V_{\text{ESD}} & \text{electrostatic discharge voltage} & \text{MM} \ \text{(JEDEC JESD22-A115)} & 200 & - \\ \hline \textbf{Source-drain diode} & \\ \hline I_{S} & \text{source current} & T_{mb} = 25 \ ^{\circ}\text{C} & - & 55 \\ \hline I_{SM} & \text{peak source current} & \text{pulsed}; \ t_p \leq 10 \ \mu\text{s}; \ T_{mb} = 25 \ ^{\circ}\text{C} & - & 336 \\ \hline \textbf{Avalanche rugedness} & \end{array}$	V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	25	V
$V_{GS} = 10 V; T_{mb} = 100 °C; see Figure 1$ -60 $I_{DM}$ peak drain currentpulsed; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 °C;$ see Figure 4-336 $P_{tot}$ total power dissipation $T_{mb} = 25 °C;$ see Figure 2-61 $T_{stg}$ storage temperature-55175 $T_j$ junction temperature-55175 $T_{sld(M)}$ peak soldering temperature-260 $V_{ESD}$ electrostatic discharge voltageMM (JEDEC JESD22-A115)200-Source-drain diode $I_S$ source current $T_{mb} = 25 °C$ -55 $I_{SM}$ peak source currentpulsed; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 °C$ -336	V <sub>GS</sub>	gate-source voltage		-20	20	V
IDMpeak drain currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C;$ -336P_tottotal power dissipation $T_{mb} = 25 \ ^{\circ}C;$ see Figure 2-61T_stgstorage temperature-55175Tjjunction temperature-55175T_sld(M)peak soldering temperature-260V_ESDelectrostatic discharge voltageMM (JEDEC JESD22-A115)200-Source-drain diodeT_mb = 25 \ ^{\circ}C-55155Issource currentT_mb = 25 \ ^{\circ}C-55Ispeak source currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$ -336Avalanche ruggedness-5536	I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	84	А
see Figure 4 $P_{tot}$ total power dissipation $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 2-61 $T_{stg}$ storage temperature-55175 $T_j$ junction temperature-55175 $T_{sld(M)}$ peak soldering temperature-260 $V_{ESD}$ electrostatic discharge voltageMM (JEDEC JESD22-A115)200-Source-drain diode $I_s$ source current $T_{mb} = 25 \ ^{\circ}C$ -55 $I_{SM}$ peak source currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$ -336Avalanche rugedness			$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	60	А
$T_{stg}$ storage temperature-55175 $T_j$ junction temperature-55175 $T_{sld(M)}$ peak soldering temperature-260 $V_{ESD}$ electrostatic discharge voltageMM (JEDEC JESD22-A115)200-Source-drain diodeIssource current $T_{mb} = 25 \ ^{\circ}C$ -55I <sub>SM</sub> peak source currentpulsed; t <sub>p</sub> ≤ 10 µs; $T_{mb} = 25 \ ^{\circ}C$ -336Avalanche rugedness	I <sub>DM</sub>	peak drain current		-	336	A
Tjjunction temperature-55175T_{sld(M)}peak soldering temperature-260V_ESDelectrostatic discharge voltageMM (JEDEC JESD22-A115)200-Source-drain diodeIssource current $T_{mb} = 25 \ ^{\circ}C$ -55IsMpeak source currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$ -336Avalanche ruggedness	P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	61	W
T sld(M)peak soldering temperature-260V ESDelectrostatic discharge voltageMM (JEDEC JESD22-A115)200-Source-drain diodeIIssource currentT mb = 25 °C-55IsMpeak source currentpulsed; tp ≤ 10 µs; T mb = 25 °C-336Avalanche ruggedness	T <sub>stg</sub>	storage temperature		-55	175	°C
$\begin{tabular}{ c c c c c } \hline V_{ESD} & electrostatic discharge voltage & MM (JEDEC JESD22-A115) & 200 & - \\ \hline Source-drain diode & & & & \\ \hline I_S & source current & T_{mb} = 25 \ ^{\circ}C & - & 55 \\ \hline I_{SM} & peak source current & pulsed; t_p \leq 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C & - & 336 \\ \hline Avalanche ruggedness & & & & \\ \hline \end{array}$	Tj	junction temperature		-55	175	°C
Source-drain diodeTmb = 25 °C-55Ispeak source currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 °C$ -336Avalanche ruggedness	T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Issource current $T_{mb} = 25 \ ^{\circ}C$ -55IsMpeak source currentpulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$ -336Avalanche ruggedness	V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	200	-	V
$I_{SM} \qquad \text{peak source current} \qquad \text{pulsed; } t_p \le 10 \ \mu\text{s; } T_{mb} = 25 \ ^\circ\text{C} \qquad - 336$ Avalanche ruggedness	Source-drain	n diode				
Avalanche ruggedness	ls	source current	T <sub>mb</sub> = 25 °C	-	55	А
	I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	336	А
$E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \text{ V}; T_{i(init)} = 25 \text{ °C}; I_D = 84 \text{ A};$ - 17.4	Avalanche ru	uggedness				
	E <sub>DS(AL)S</sub>	non-repetitive drain-source	$V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ I}_{D} = 84 \text{ A};$	-	17.4	mJ

avalanche energy

see Figure 3

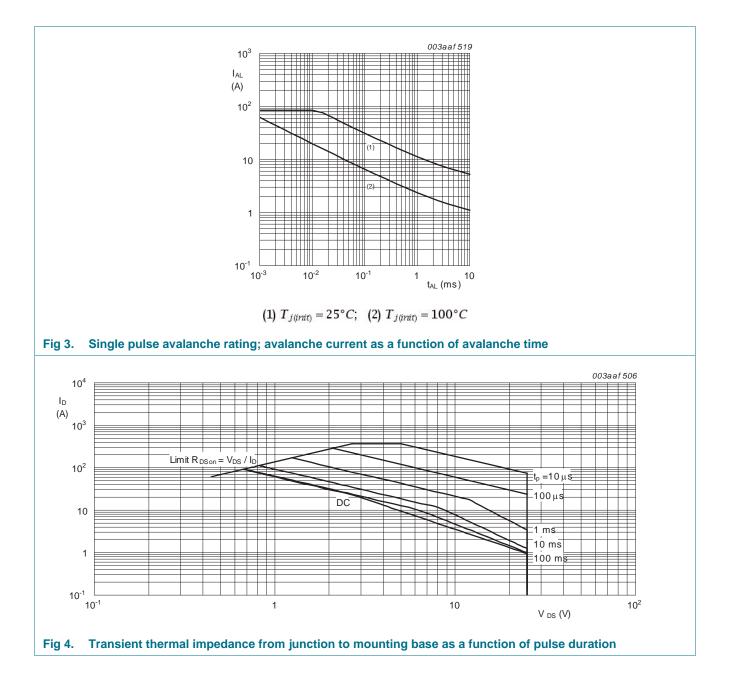








# PSMN4R0-25YLC



N-channel 25 V 4.5 m $\Omega$  logic level MOSFET in LFPAK

### 5. Thermal characteristics

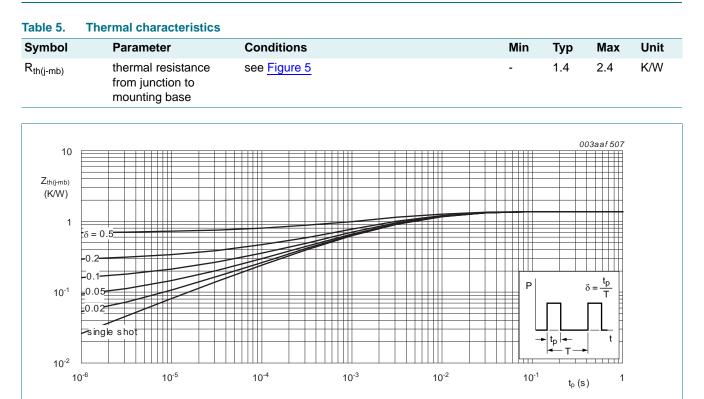


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

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N-channel 25 V 4.5 mΩ logic level MOSFET in LFPAK

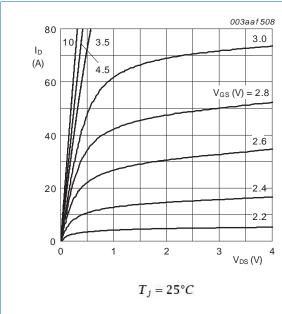
### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	25	-	-	V
	breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	22.5	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	1.05	1.53	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ see <u>Figure 11</u>	0.5	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	4.5	5.8	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 20 A; $T_j$ = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	9.85	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	3.5	4.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	7.65	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	2.1	4.2	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	22.8	-	nC
		$I_D = 0 \text{ A};  V_{DS} = 0  \text{V};  V_{GS} = 10  \text{V};$ see Figure 14	-	21.1	-	nC
		$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	10.9	-	nC
Q <sub>GS</sub>	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	3.3	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	2.25	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	1.05	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 20 \text{ A}; V_{DS} 12 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	3.5	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 12 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	2.58	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	1407	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	354	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	119	-	pF

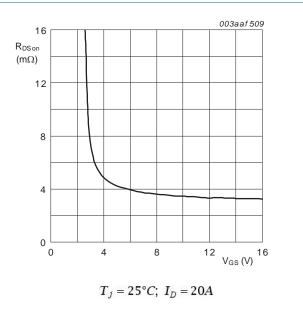
PSMN4R0-25YLC

# PSMN4R0-25YLC

Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 12 V; $R_L$ = 0.5 $\Omega; ~V_{GS}$ = 4.5 V;	-	15.9	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	17.5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	24	-	ns
t <sub>f</sub>	fall time		-	9.9	-	ns
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	7.32	-	nC
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 20 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$	-	24.5	-	ns
Qr	recovered charge	$V_{DS} = 12 V$	-	16.1	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$ $V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 18}{100000000000000000000000000000000000$	-	14.9	-	ns
t <sub>b</sub>	reverse recovery fall time		-	9.6	-	ns

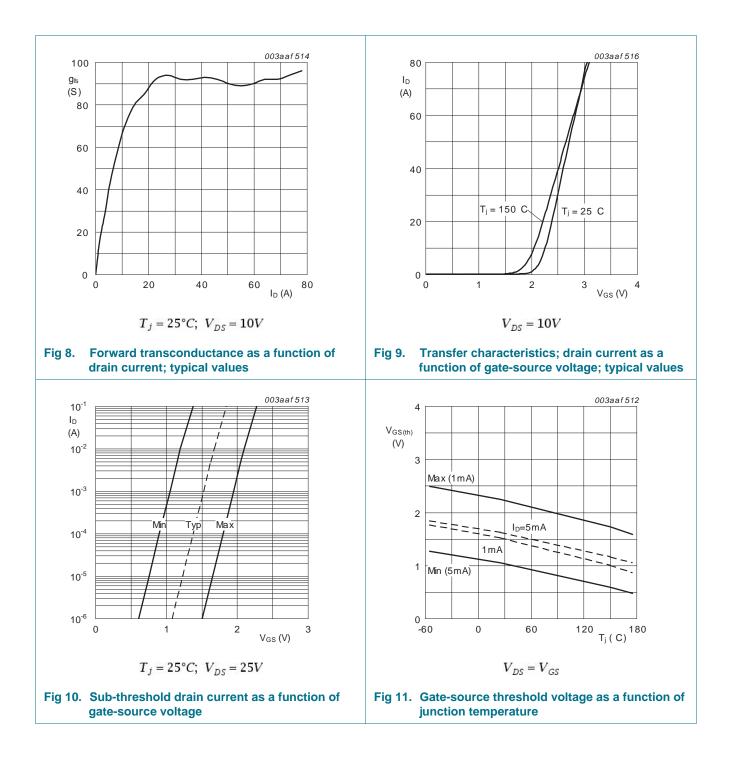




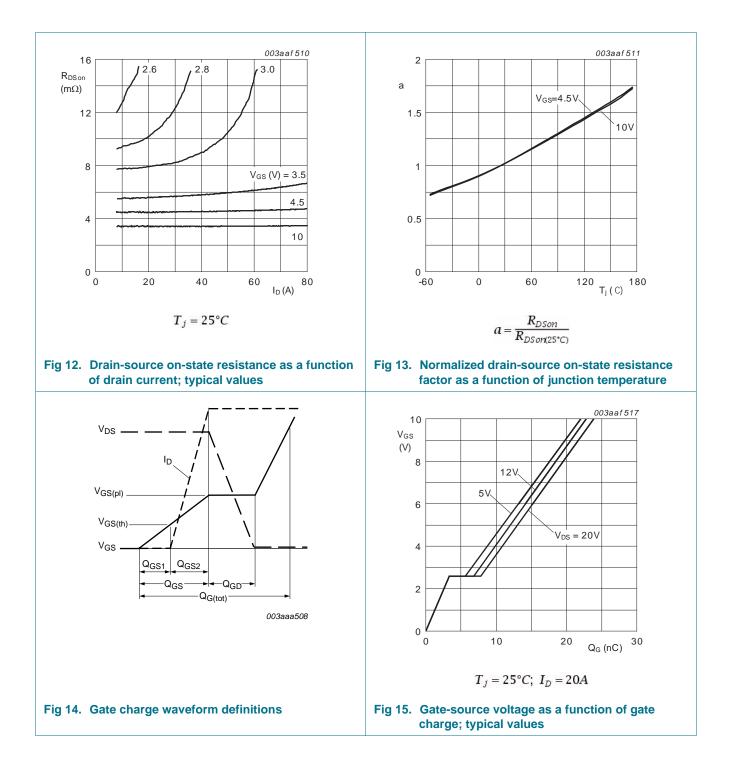




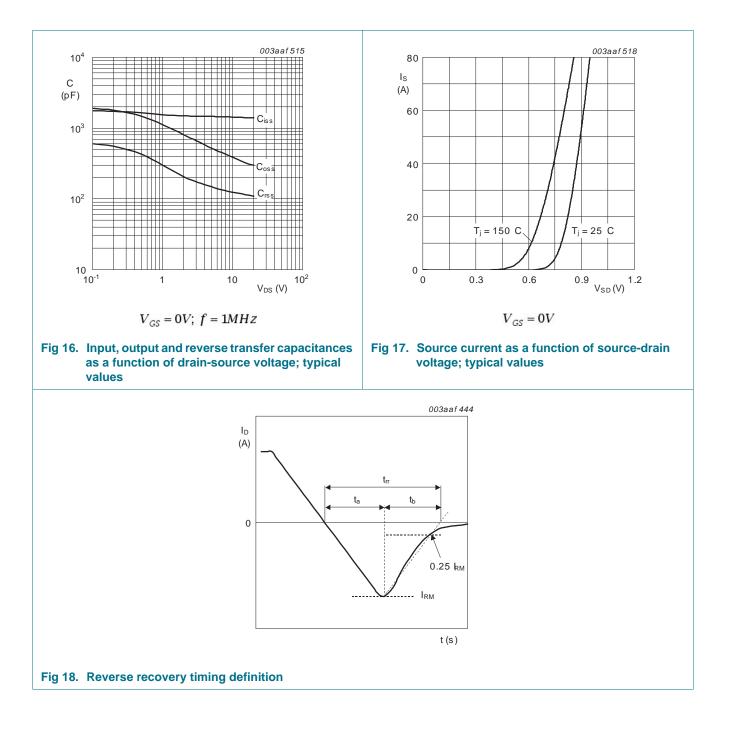
# PSMN4R0-25YLC



# PSMN4R0-25YLC

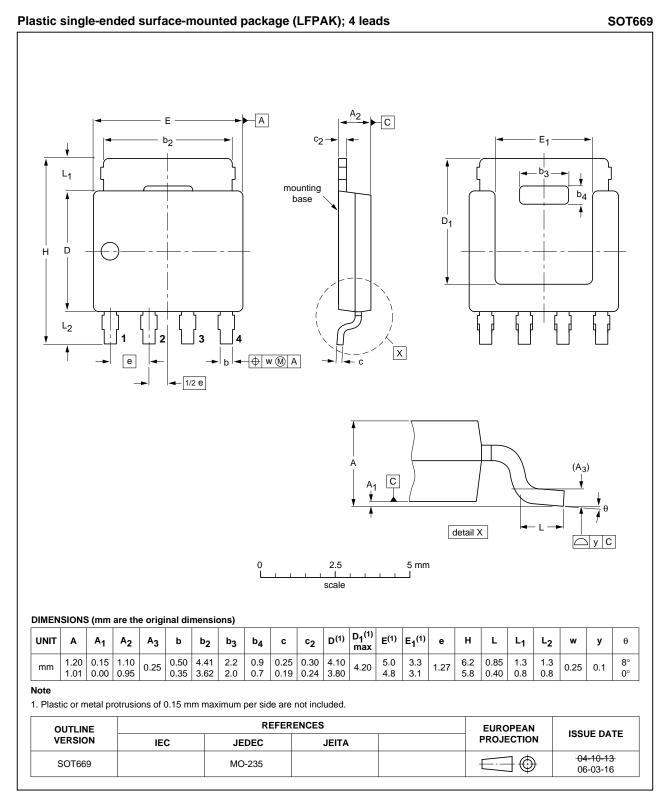


## PSMN4R0-25YLC



N-channel 25 V 4.5 m $\Omega$  logic level MOSFET in LFPAK

### 7. Package outline



#### Fig 19. Package outline SOT669 (LFPAK)

All information	provided in t	his	document	is	subject to	legal	disclaimers.

PSMN4R0-25YLC

### N-channel 25 V 4.5 mΩ logic level MOSFET in LFPAK

### 8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R0-25YLC v.1	20101202	Product data sheet	-	-

N-channel 25 V 4.5 m $\Omega$  logic level MOSFET in LFPAK

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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